Philips Semiconductors

Three quadrant triacs guaranteed commutation

BTA216 series D, E and F

GENERAL DESCRIPTION

QUICK REFERENCE DATA

Passivated guaranteed commutation triacs in a plastic envelope intended for use in motor control circuits or with other highly inductive loads. These devices balance the requirements of commutation performance and gate sensitivity. The "sensitive gate" E series and "logic level" D series are intended for interfacing with low power drivers, including micro controllers.

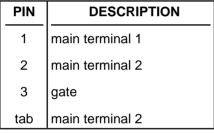
| SYMBOL | PARAMETER | MAX. | MAX. | UNIT |
|---|--|----------------------|-------------------|--------|
| | BTA216- BTA216- BTA216- | 600D 600E 600F | - 800E 800F | |
| V_{DRM} | Repetitive peak off-state | 600 | 800 | V |
| I _{T(RMS)} I _{TSM} | voltages RMS on-state current Non-repetitive peak on-state current | 16 140 | 16 140 | A A |

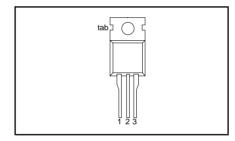
PINNING - TO220AB

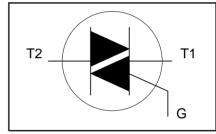
| MOIT | |
|------|--|
| | |

PIN CONFIGURATION

SYMBOL







LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MA | X. | UNIT |
|---|---|--|-------------|---------------------------------|--------------------|------------------|
| V_{DRM} | Repetitive peak off-state voltages | | - | -600 600 ¹ | -800 800 | V |
| I _{T(RMS)} | RMS on-state current | full sine wave; | - | 16 | 6 | Α |
| I _{TSM} | Non-repetitive peak on-state current | $T_{mb} \le 99$ °C full sine wave; $T_{j} = 25$ °C prior to surge $t = 20$ ms | | 14 | 0 | A |
| | | t = 20 ms | - | 15 | | |
| l²t dl _⊤ /dt | I ² t for fusing Repetitive rate of rise of on-state current after triggering | t = 10 ms $I_{TM} = 20 \text{ A}; I_{G} = 0.2 \text{ A};$ $dI_{G}/dt = 0.2 \text{ A}/\mu\text{s}$ | - | 98 | 3 | Α A²s A/μs |
| I _{GM} V _{GM} P _{GM} P _{G(AV)} | Peak gate current Peak gate voltage Peak gate power Average gate power | over any 20 ms | - - - | 2 5 5 0. | | A V W W |
| T_{stg}^{stg} | Storage temperature Operating junction temperature | ponou | -40 - | 15 12 | | °C °C |

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¹ Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 15 A/μs.

Philips Semiconductors Objective specification

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THERMAL RESISTANCES

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|--|---|---|------|--------------|-----------------|-------------------|
| $R_{\text{th j-mb}}$ $R_{\text{th j-a}}$ | Thermal resistance junction to mounting base Thermal resistance junction to ambient | full cycle half cycle in free air | | - - 60 | 1.2 1.7 - | K/W K/W K/W |

STATIC CHARACTERISTICS

 $T_i = 25$ °C unless otherwise stated

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | | MAX. | | UNIT |
|----------------|-----------------------------------|---|------|------|--------|----------|----------|----------|
| | | BTA216- | | | D | Е | F | |
| $I_{\rm GT}$ | Gate trigger current ² | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$ | | | _ | 40 | 25 | A |
| | | T2+ G+ T2+ G- | _ | _ | 5 | 10 10 | 25 25 | mA mA |
| | | T2- G- | _ | _ | 5 5 | 10 | 25 | mA |
| I _L | Latching current | $V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$ | | | | ' | | |
| _ | | T2+ G+ | - | - | 15 | 20 | 25 | mA |
| | | T2+ G- | - | - | 25 | 30 | 40 | mA |
| | | T2- G- | - | - | 25 | 30 | 40 | mA |
| I _H | Holding current | $V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$ | - | - | 15 | 25 | 30 | mA |
| V_T | On-state voltage | I _τ = 20 A | - | 1.2 | | 1.5 | | V |
| V'_{GT} | Gate trigger voltage | $\dot{V}_{D} = 12 \text{ V}; I_{T} = 0.1 \text{ A}$ | - | 0.7 | | 1.5 | | V |
| | | $V_D = 400 \text{ V}; I_T = 0.1 \text{ A};$ | 0.25 | 0.4 | | - | | V |
| | Off state leakage surrent | T _j = 125 °C | | 0.1 | | 0.5 | | A |
| I_D | Off-state leakage current | $V_D = V_{DRM(max)};$ $T_i = 125 \degree C$ | - | 0.1 | | 0.5 | | mA |

DYNAMIC CHARACTERISTICS

 $T_i = 25$ °C unless otherwise stated

| SYMBOL | PARAMETER | CONDITIONS | | MIN. | | TYP. | MAX. | UNIT |
|-----------------------|--|---|-----|------|-----|------|------|------|
| | | BTA216- | D | Е | F | | | |
| dV _D /dt | Critical rate of rise of off-state voltage | V _{DM} = 67% V _{DRM(max)} ; T _j = 110 °C; exponential waveform; gate open circuit | 30 | 60 | 70 | - | - | V/μs |
| dl _{com} /dt | Critical rate of change of commutating current | $V_{DM} = 400 \text{ V}; T_j = 110 ^{\circ}\text{C};$ $I_{T(RMS)} = 16 \text{ A};$ $dV_{com}/dt = 20v/\mu\text{s}; \text{ gate}$ open circuit | 1.8 | 3.5 | 4.5 | - | - | A/ms |
| dI _{com} /dt | Critical rate of change of commutating current | $\label{eq:DM} \begin{array}{l} V_{DM} = 400 \text{ V; } T_j = 110 \text{ °C;} \\ I_{T(RMS)} = 16 \text{ A;} \\ dV_{com}/dt = 0.1 \text{v/}\mu\text{s; gate} \\ open circuit \end{array}$ | 4.3 | 5.3 | 6.3 | - | - | A/ms |
| t _{gt} | Gate controlled turn-on time | $I_{TM} = 20 \text{ A; } V_D = V_{DRM(max)}; \\ I_G = 0.1 \text{ A; } dI_G/dt = 5 \text{ A}/\mu s$ | - | - | - | 2 | - | μs |

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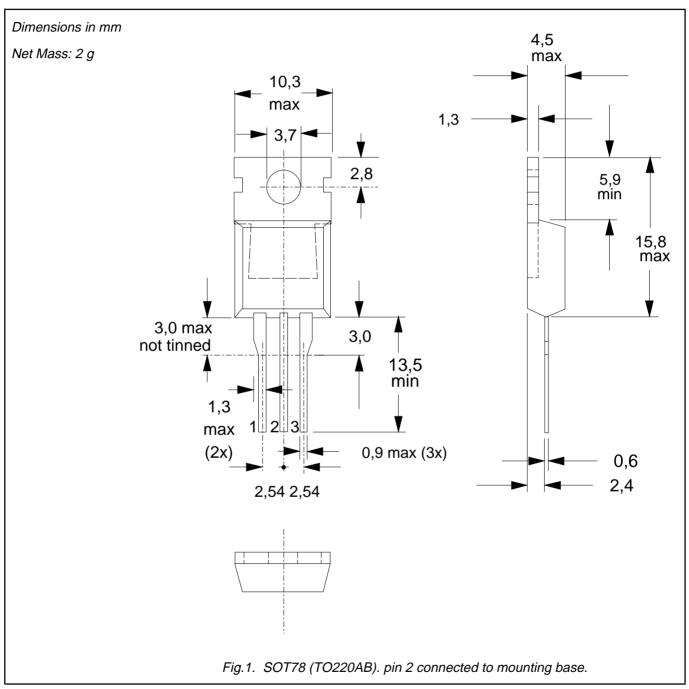
² Device does not trigger in the T2-, G+ quadrant.

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MECHANICAL DATA



- Refer to mounting instructions for SOT78 (TO220) envelopes.
 Epoxy meets UL94 V0 at 1/8".

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Objective specification

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DEFINITIONS

| Data sheet status | | | | | |
|--|---|--|--|--|--|
| Objective specification | This data sheet contains target or goal specifications for product development. | | | | |
| Preliminary specification | This data sheet contains preliminary data; supplementary data may be published later. | | | | |
| Product specification This data sheet contains final product specifications. | | | | | |
| Limiting values | | | | | |

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

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